

BUK9219-55A

N-channel TrenchMOS logic level FET Rev. 02 — 7 June 2010

Product data sheet

Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	55	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	114	W



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}}$	-	-	20	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	14	17.6 r	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}}$	-	15	19	mΩ
Avalanche i	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 49 \text{ A; } V_{\text{sup}} \leq 55 \text{ V;} \\ R_{\text{GS}} &= 50 \Omega; V_{\text{GS}} = 5 \text{ V;} \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C; } \text{ unclamped} \end{split}$	-	-	120	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EA)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9219-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

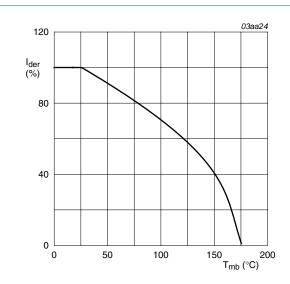
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V_{GS}	gate-source voltage			-10	-	10	V
I _D	drain current	$T_{mb} = 100 ^{\circ}C; V_{GS} = 5 V; \text{see } \frac{\text{Figure 1}}{}$		-	-	38	Α
		T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>		-	-	55	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; t_p ≤ 10 μs; pulsed; see Figure 3	[1]	-	-	219	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	114	W
T _{stg}	storage temperature			-55	-	175	°C
T _j	junction temperature			-55	-	175	°C
V_{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \mu s$		-15	-	15	V
Source-drain	n diode						
Is	source current	T _{mb} = 25 °C		-	-	55	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	219	Α
Avalanche ru	uggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 49 \text{ A; } V_{sup} \leq 55 \text{ V; } R_{GS} = 50 \Omega; \\ V_{GS} &= 5 \text{ V; } T_{j(init)} = 25 \text{ °C; } unclamped \end{split}$		-	-	120	mJ

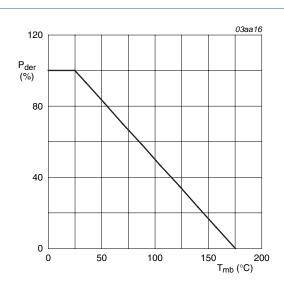
^[1] peak drain current is limited by chip, not package.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

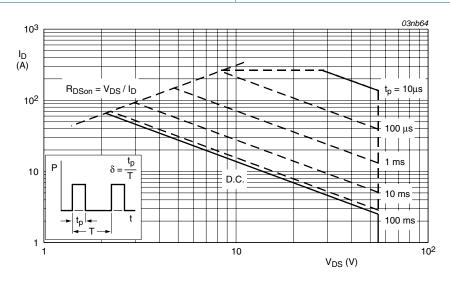
function of mounting base temperature

Normalized continuous drain current as a



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Normalized total power dissipation as a function of mounting base temperature Fig 2.



 $T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; FR4 board	-	71.4	-	K/W

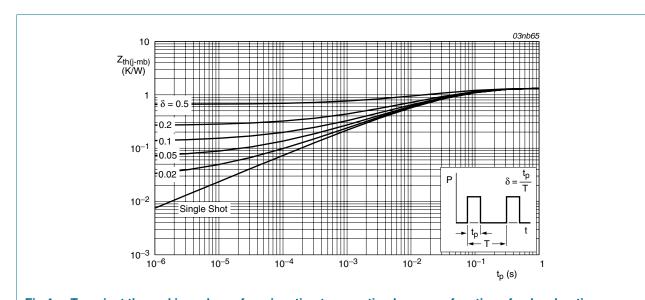


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	٧
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	٧
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 11	1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 11</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 175 \text{ °C}$; see Figure 12; see Figure 13	-	-	38	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	20 17.6	mΩ
		$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 12; see Figure 13	-	14	17.6	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	15	19	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	2190	2920	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	380	450	pF
C _{rss}	reverse transfer capacitance		-	250	345	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	45	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	130	-	ns
t _{d(off)}	turn-off delay time		-	400	-	ns
t _f	fall time		-	130	-	ns
L _D	internal drain inductance	measured from drain lead from package to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead from package to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode	·				
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 15	-	0.85	1.2	V
+	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = -10 \text{ V};$	_	51	_	ns
t _{rr}	reverse recovery time	$V_{DS} = 30 \text{ V}; T_i = 25 \text{ °C}$		•		

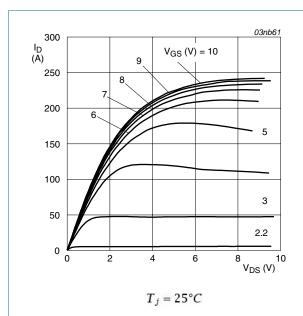


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

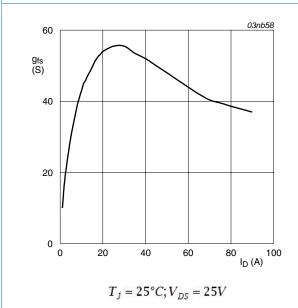
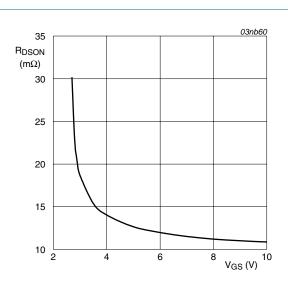
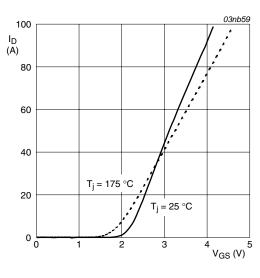


Fig 7. Forward transconductance as a function of drain current; typical values



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. On-state resistance: typical values



 $V_{DS} = 25V$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

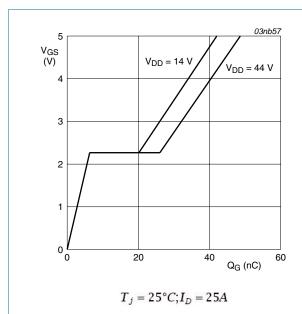


Fig 9. Gate-source voltage as a function of turn-on gate charge; typical values

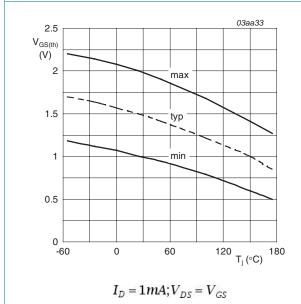


Fig 11. Gate-source threshold voltage as a function of junction temperature

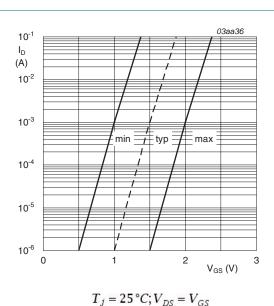


Fig 10. Sub-threshold drain current as a function of

gate-source voltage

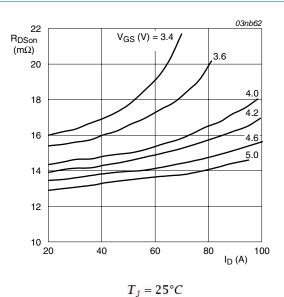


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

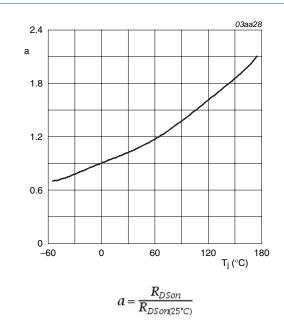
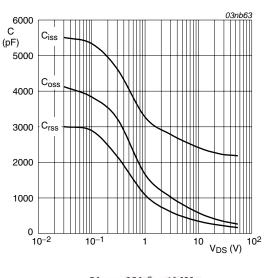


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



$$V_{GS} = 0V; f = 1MHz$$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

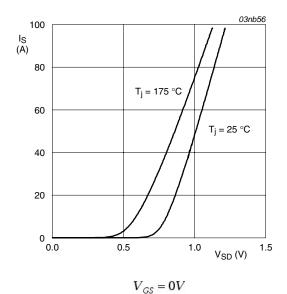


Fig 15. Reverse diode current; typical value

7. Package outline

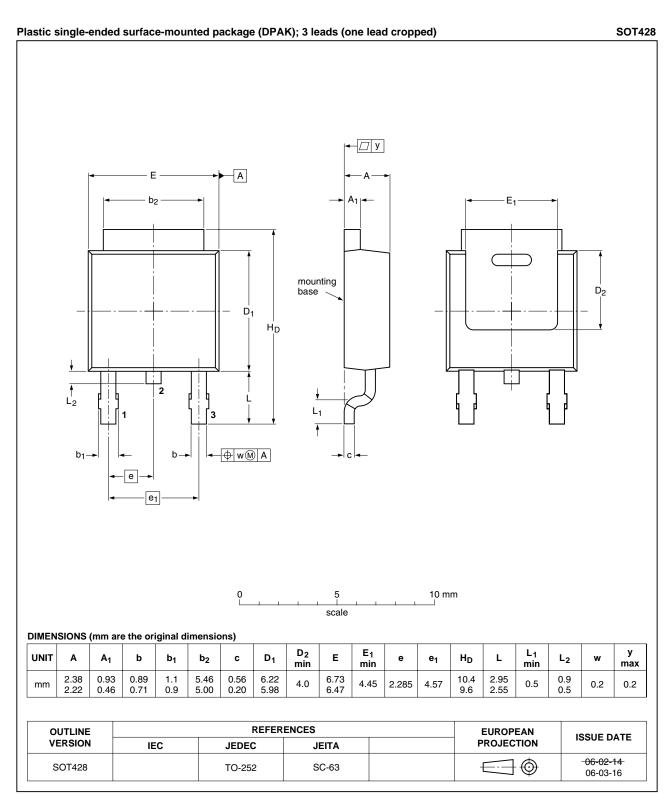


Fig 16. Package outline SOT428 (DPAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9219-55A_2	20100607	Product data sheet	-	BUK9219-55A_1
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidel of NXP Semiconductors. 			
	 Legal texts 	have been adapted to the	new company name wh	ere appropriate.
BUK9219-55A_1	20001024	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel TrenchMOS logic level FET

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